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ORIGINAL ARTICLE

TRANSCONDUCTANCE AND TRANSFER CHARACTERISTICS OF 8 MEV ELECTRON IRRADIATED DUAL N-CHANNEL MOSFETS

Godwin Jacob D' Souza
Associate Professor, Dept. of Electronics, St Joseph's College (Autonomous)
Bangalore .

ABSTRACT:

The electrical qualities of double N-channel upgrade metal-oxide semiconductor field-impact semiconductors (MOSFETs) were modified by lighting with 8 MeV electron bar for various dosages going from 200 Gy to 1 kGy at encompassing air. The light examinations were led with door inclination (VGS = −2, 0, +1.5 and +2 V). Critical expansion in transconductance (g_m) was seen after light. The gm was found to increment radically for the portion of 1 kGy with positive inclination (1.5 and 2 V). The exchange qualities at VDS=12 V uncovered that the channel current (I_D) increments with the increment of portion and furthermore increments with the increment of entryway predisposition voltage during illumination. The aftereffects of these examinations are introduced and talked about.

KEYWORDS — MOSFET, Radiation effect, Electron radiation, Transconductance, Transfer Characteristics, Si/SiO2 interface.

INTRODUCTION

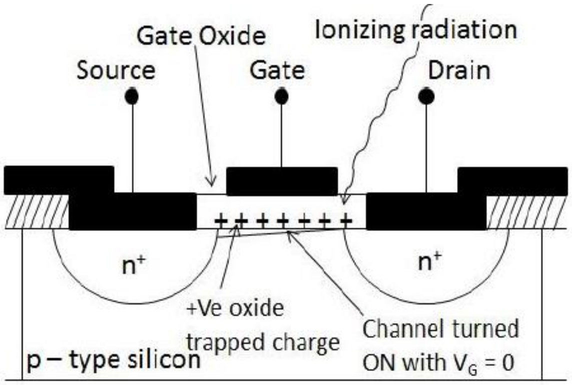
Throughout recent many years, semiconductors have become generally significant material for the creation of electronic and optoelectronic gadgets. The creation of semiconductors just about quite a while back has brought about the improvement of present day society with cutting edge data frameworks. The electronic frameworks left ready of space apparatus' are submitted to extremely durable brilliance of either inestimable or sunlight based beginning. These radiations might cause breaking down of electronic gadgets and parts. The investigation of radiation prompted absconds in semiconductors would be very helpful in assessing the lifetime of gadgets working in radiation climate, for example, space applications, nuclear energy establishments and so on. Metal-oxide semiconductor (MOS) gadgets are among the most delicate of all semiconductors to radiation, specifically ionizing radiation, showing a lot of progress even after a generally low portion and are inclined to parametric or even practical disappointment on openness to radiation conditions. In metal-oxide semiconductor field-impact semiconductors (MOSFETs), the entryway oxide structures effect on the progressions in the electrical attributes because of illumination.

In light of their quicker exchanging velocities and basic drive prerequisites, MOSFETs are liked for our examination. An endeavor has been made to comprehend the impact of 8 MeV electron shaft on double n-channel MOSFETs.

IONIZING RADIATION EFFECTS ON MOSFETS

The MOSFET is a four-terminal gadget comprising of a p-type Si substrate with n+ source and channel districts isolated by a channel, which is covered by a meager protecting film (SiO_2) with a metal or polysilicon door cathode on the separator. The essential activity of this gadget comprises of applying voltage to the door, which causes the p-type substrate to upset the locale close to the SiO_2/Si interface under the entryway, making a conduction way for electrons among source and channel. As the entryway voltage is expanded, the current among source and channel increments for a given channel voltage until immersion is reached.

Figure 1. Schematic illustration of an n-channel MOSFET during the ionizing radiation on the gate oxide



At the point when MOS gadgets are presented to 8 MeV electrons, these high-energy electrons effectively go through the entryway oxide layer. These electrons move energy into the MOSFET through electronic excitations, which thus produce ionization or breaking bonds and dislodging of iotas along its way during the light cycle.

A portion of the emphatically charged openings are caught at the Si/SiO_2 interface which brings about extra oxide charge and decreases the limit voltage. Thus, there is important to concentrate on the progressions in move and transconductance qualities of the gadget because of high energy radiation.

Figure 2. Experimental setup made for irradiation at Microtron Centre

DEVICES AND METHODS

In this review, we have utilized the solid double N-channel and double P-channel matched semiconductor sets of improvement mode MOSFETs (ALD1103) with 14-Pin plastic Plunge bundle obtained from Cutting edge Power Parts, UK for light examinations. The gadgets were lighted with 8 MeV electron pillar (displayed in figure 2) for the portions going from 200 Gy to 1 kGy in strides of 200 Gy, utilizing variable energy Microtron gas pedal College, India. The elements of the Microtron are nitty gritty somewhere else. Likewise, the gadgets were lighted for various door predisposition (V_{GS} = −2, 0, +1.5 and +2 V) at room temperature. The electrical portrayal of the non-illuminated and 8MeV electron-lighted N-channel MOSFETs were performed utilizing PC connected Keithley 2612A source measure unit. The ongoing goal with the test arrangement was of the request for 1-100 Dad. Point by point studies were completed on the transconductance and move qualities of n-channel MOSFET gadgets and the outcomes are introduced and talked about in this.

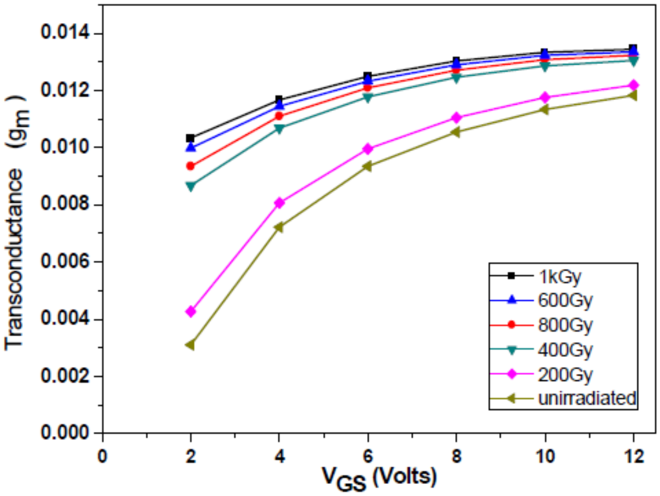
RESULT AND DISCUSSION

- **Transconductance**

The transconductance (g_m) of the not entirely settled from the channel current (I_D) versus entryway source voltage (V_{GS}) qualities characterized as the pace of expansion in I_D per unit expansion in V_{GS} at fixed channel source voltage (VDS) [11], for example

The essential impact of ionizing radiation is to deliver electron-opening matches in the thermally developed separator and furthermore causes extra connection point traps to be framed at the Si/SiO_2 interface. Following figure addresses the variety of transconductance of the N-channel MOSFETs for when light. There is an uncommon expansion in g_m after 200 Gy electron light and no huge changes from 400 Gy to 1 kGy.

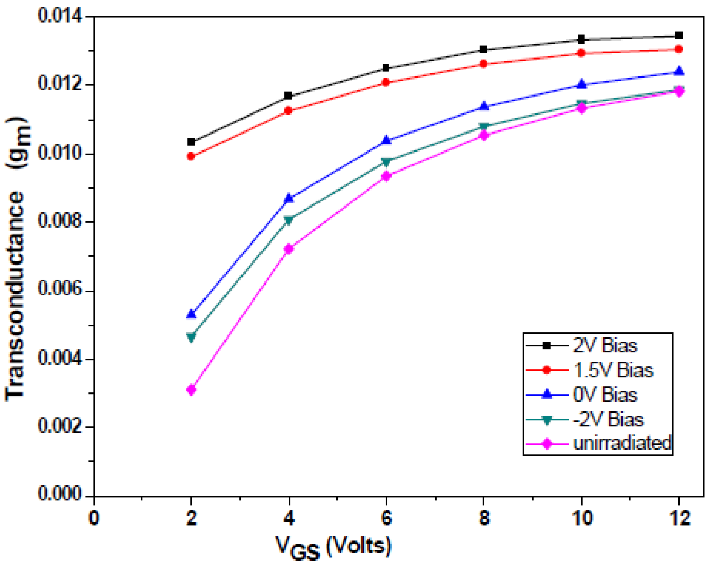
Figure 3. Variation of g_m versus V_{GS} with respect to electron dose (at V_{DS} = 12 V)



In the upgrade MOSFETs, predisposition voltage is important to improve the channel to stream channel to-source current, on account of the gadget is totally disengaged and there is no ongoing stream at V_{GS} =0 V. Following figure shows the impact of inclination voltage on the g_m of the 8 MeV electron lighted MOSFET for the portion of 1 kGy during illumination. The door inclination during light upgrades the gadget execution by giving channel i.e., by reversing the p-type substrate adequately to cause a current of something like 1 A to stream among source and channel.

Likewise, g_m of the lighted gadgets increments definitely subsequent to applying the forward predisposition of 1.5 and 2 V individually. Further, there is a decline in the g_m because of converse predisposition of - 2 V contrasted with positive inclination ie., more prominent than 0 V.

Figure 4. Variation of gm verses VGS with respect to gate bias during irradiation (at Dose = 1 kGy & VDS = 12 V)



The pinnacle transconductance (g_{mPeak}) was separated from the ID versus VGS plot taken at VDS = 12 V and upsides of gmPeak after 8 MeV electron light of various portion were given in table 1. It tends to be seen that around 1 to 10% expansions in the g_{mPeak} after an all out portion of 1 kGy for various entryway predisposition during illumination. The greatest g_{mPeak} was noticed for gadget lighted with 1 kGy portion with positive door inclination of 2 V. This is because of diminished caught openings and connection point traps which debilitates the transporters moving in to the channel and thus increment the transconductance. Comparable pattern of perception was made with decline in g_{mPeak} after absolute portion illumination if there should arise an occurrence of double entryway exhaustion mode.

TABLE 1 Variation In gmpeak After 8 Mev Electron Irradiation Taken at VDS = VGS = 12V For Different Biasing Voltage During Irradiation

Electron Dose	**Peak Transconductance (g_{mPeak})**			
	V_{GS}= 2V Bias	**V_{GS}= 1.5V Bias**	**V_{GS}= 0V Bias**	**V_{GS}= -2V Bias**
200 Gy	0.01221	0.01189	0.01211	0.01171
400 Gy	0.01312	0.01272	0.01223	0.01174
600 Gy	0.01339	0.01292	0.01234	0.01189
800 Gy	0.01329	0.01290	0.01237	0.01187
1000 Gy	0.01348	0.01314	0.01243	0.01192

Transfer Characteristics

The exchange trademark relates channel current (I_D) reaction to the information entryway source driving voltage (V_{GS}) for a proper channel source voltage (V_{DS}). Since the entryway terminal is electrically segregated from the leftover terminals (channel, source, and mass), the door flow is basically zero, so that entryway flow isn't important for gadget qualities. The exchange trademark bend can find the entryway voltage at which the semiconductor passes current and leaves the OFF-state. Likewise, it is helpful for picturing the addition from the gadget and recognizing the area of linearity. The door voltage at which the ongoing turns on is known as the edge voltage, V_T. For the ALD1103, the information sheet gives V_T = 0.4 V to 1 V, depending of V_{DS}.

Figure 5. Transfer Characteristics of 8 MeV electron irradiated MOSFETs (at VGS=2V Bias) with different dose (VDS=12V)

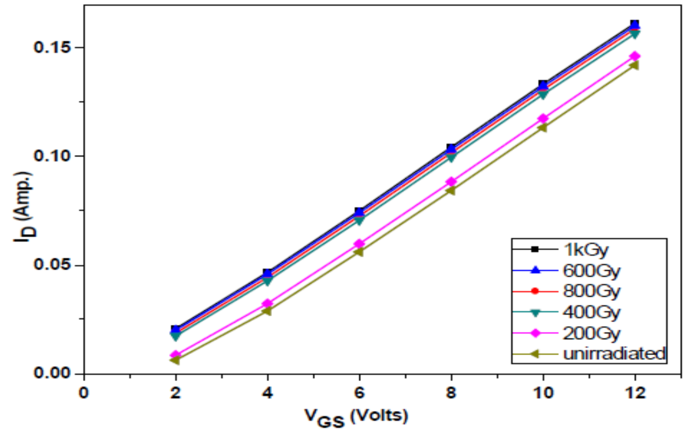


Figure 6. Transfer Characteristics of 8 MeV electron irradiated MOSFETs (at 1 kGy dose) for different bias voltage (VDS=12V)

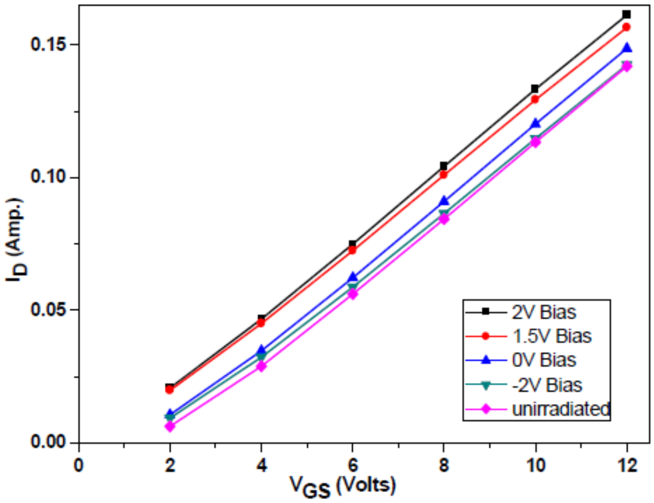


Figure 5 and 6 portray the exchange qualities (I_D versus V_{GS}) of 8 MeV electron lighted MOSFETs at V_{DS} = 12 V. In figure 5, it is obviously seen that the I_D increments with the increment of portion. And furthermore I_D increments with the increment of entryway predisposition voltage during illumination which is confirmed in figure 6. The I_D was expanded because of the change in limit voltage and it is a resultant impact of both caught charges at Si/SiO_2 surface and in mass oxide.

Conclusions:

The impact of 8 MeV electron radiation on double N-channel MOSFETs were examined and it was seen that, the transconductance and move trademark increments with electron portion as well as certain door predisposition during light. Top transconductance g_{mpeak} was expanded around 1 to 10% after a complete portion of 1 kGy for various door inclinations. The outcomes show that the double N-channel MOSFET is exceptionally delicate to radiation climate.

REFERENCES

- Bhat, B. R. Sahu, R. P. Radiation Shielding of Electronic Components in INSAT-2. Journal of Spacecraft Technology, 3
- Buchman, P. Total Dose Hardness Assurance for Microcircuits for Space Environment. IEEE Trans. Nucl. Sci. NS-33(6), 98 (1986), 1352-1358.
- Gnana Prakash, A.P. Prashanth, K. C. Ganesh, Nagesha, Y. N. Umakanth, D. Arora, S. K. Siddappa, K. Effect of 30 MeV Li3+ ion and 8 MeV electron irradiation on N-channel MOSFETs. 157(3) (2002), 323-331.
- Ganesh, Prashanth, K. C. Nagesh, Y. N. Gnana Prakash, A. P. Umakanth, D. Pattabi, M. Siddappa, K. Salkalachen, S. Roy, A. Modification of power diode characteristics using bremsstrahlung radiation from microtron. Radiat. Phys. Chem. 55 (1999), 461–464.
- Gnana Prakash, A. P. Ke, S. C. Siddappa, K. High-energy radiation effects on subthreshold characteristics, transconductance and mobility of n-channel MOSFETs. Semicond. Sci. Technol. 18 (12) (2003), 1037-1042.
- Jim Schwank, Total Dose Effects in MOS Devices. IEEE Nuclear Space Radiation Effects Conf., Short Course III-47, July 2002.
- Merabtine, N. Benslama, M. Benslama, A. Sadaoui, Dj. Radiation Effects on electronic circuits in a spacial environment. Semiconductor Physics, Quantum Electronics & Optoelectronics. 7(4) (2004), 395-399.
- Srour, J. R. Radiation effects on microelectronics in space. Proc. IEEE. 76(11) (1988), 1443.
- Sarles, F. W. Stanley, A. G. Roberge, J. K. Godfray, B. M. Space radiation damage measurements in the earth syncronous orbit. IEEE Trans. Aerosp. Electron. Syst. 9(6) (1973), 921-924.
- Siddappa, K. Ganesh, Ramamurthy, S. S. Soni, H. C. Srivastava, P. Sheth, Y. Hemnani. Variable energy microtron for R & D work. Radiat. Phys. Chem. 51 (4–6) (1998), 441– 442.
- Schroder, D. K. Semiconductor Material and Device Characterization (New York: Wiley) chapters IV, V (1990).